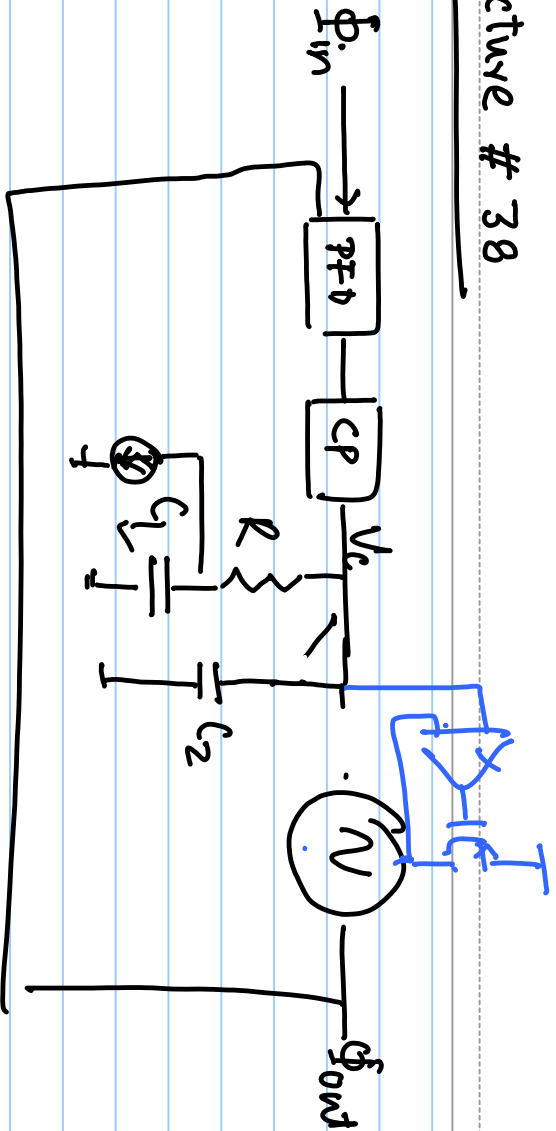


Lecture # 38

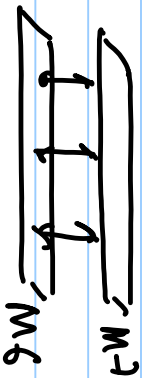


$$L_{in}(s) = \frac{1}{2\kappa} I_{cp} \left((R + 1/sC_p) \parallel 1/sC_2 \right) \frac{2\kappa k_{vco}}{\lambda}$$

$$= \frac{I_{cp} R k_{vco}}{\lambda^2 (C_2 + C_1)} \frac{(1 + sRC_1)}{(1 + sRC_1 C_2)}$$

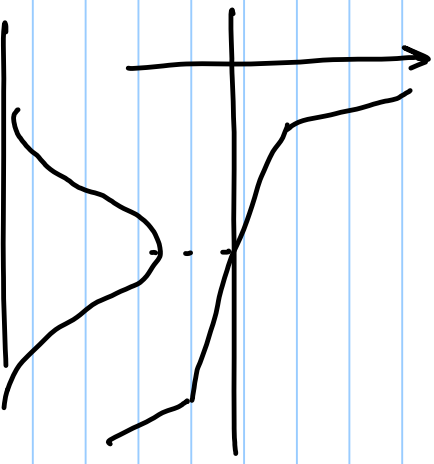
R, C : ±20%

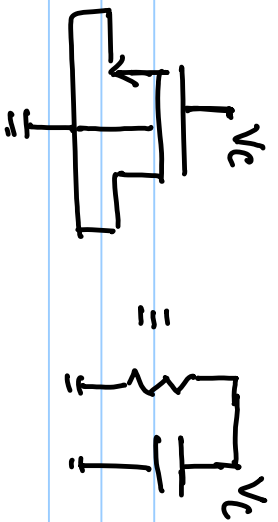
Capacitor / Min-cap / MOS cap



2 fF/μm², V_{C1} is quite low
 $\frac{dC}{dV}$

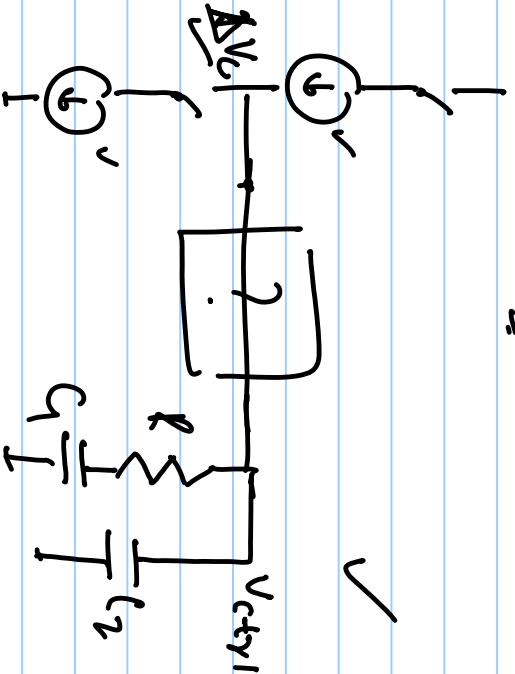
- Process variation decides C_a, R_w
- Area
- leakage current.



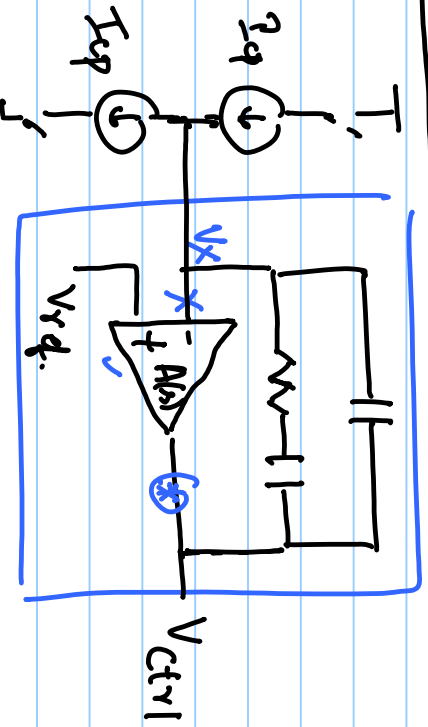


$$4 \text{ fF}/\mu\text{m}^2 \rightarrow 12 \text{ fF}/\mu\text{m}^2$$

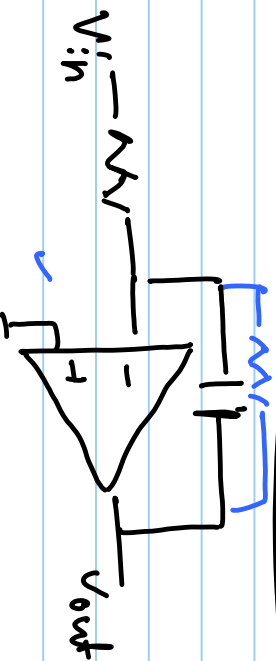
$$v_{C1} = f(\Phi_m)$$



$$\frac{V_{c1}}{I_{cp}} = \left(R + \frac{1}{sC_1} \right) \left(1 + \frac{1}{sC_2} \right) = F(s)$$

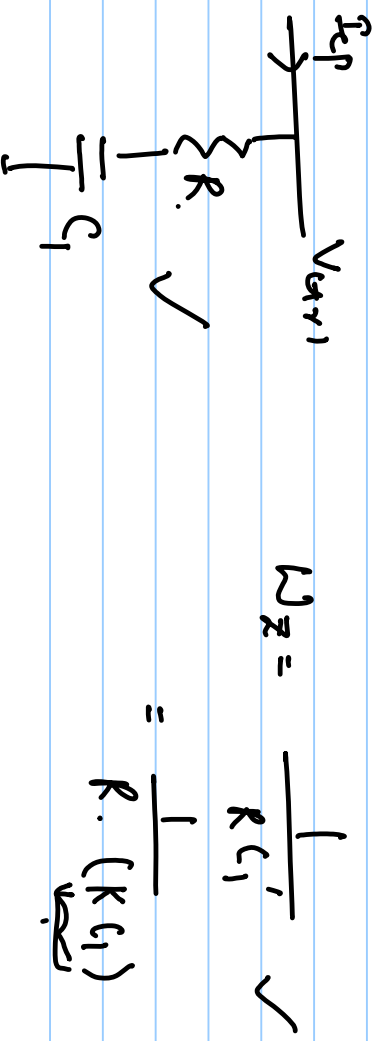


$$A(s) = \frac{A_0}{(1 + s/k_p)}$$



$$\frac{V_{out}}{I_{cp}} = -F(s) \quad F(A(s))$$

$$(V_{in} - V_x) A(s) = V_{out}$$

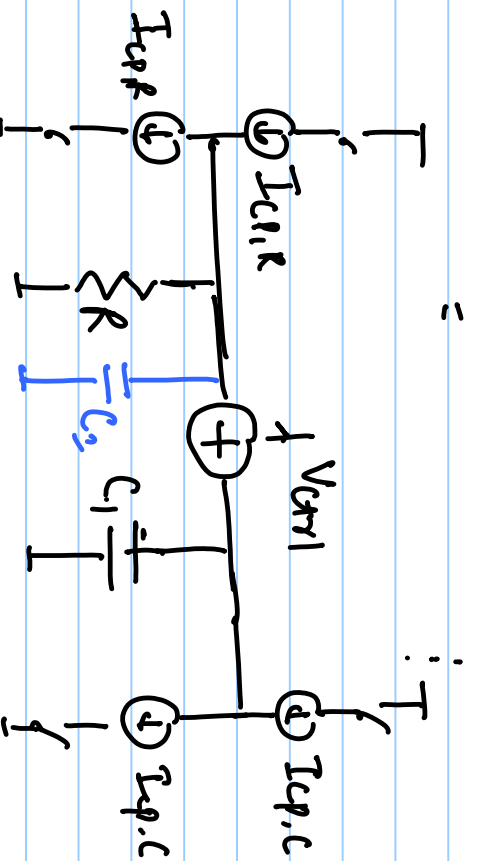


$$H_z = \frac{1}{RC_1} \quad \checkmark$$

$$= \frac{1}{R \cdot (KC_1)}$$

$$V_{out} = I_{cp} \cdot R + I_{cp} \cdot \frac{1}{sC_1}$$

$$H_z = \frac{1}{RC_1} = KR \times \frac{1}{C_1 R}$$



$$V_{out}(s) = I_{cp,R} \cdot R + I_{cp,C} \times \frac{1}{sC_1}$$

$$= I_{cp,C} \left(\frac{I_{cp,R}}{I_{cp,C}} \cdot R + \frac{1}{sC_1} \right)$$

$$= I_{cp} (K \cdot R + \frac{1}{sC_1})$$

$$\omega_z = \frac{1}{k \cdot R C_1} \quad \checkmark$$

$$V_{out}(s) = k \cdot I_{cp} \left(R \parallel \frac{1}{sC_2} \right) + I_{cp} \cdot \frac{1}{sC_1}$$

$$= I_{cp} \left[\frac{k \cdot R}{1 + sC_2 R} + \frac{1}{sC_1} \right]$$

$$= I_{cp} \left[\frac{1 + sR(C_2 + kC_1)}{sC_1(1 + sC_2 R)} \right]$$

$$\Rightarrow \omega_z = \frac{1}{R(C_2 + kC_1)} \quad , \quad \omega_{p1} = 0 \quad , \quad \omega_{p2} = \frac{1}{RC_2}$$

